

DOCKET NO: 263261US0PCT



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
HITOSHI KATO, ET AL. : EXAMINER: HARRISON, M. D.
SERIAL NO: 10/518,025 :
FILED: DECEMBER 15, 2004 , : GROUP ART UNIT: 2813
FOR: METHOD OF CVD FOR FORMING :
SILICON NITRIDE FILM ON
SUBSTRATE

AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Office Action dated September 19, 2005, Applicants respectfully request reconsideration of the above-identified application in view of the following amendment and remarks.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Discussion of the Amendment begins on page 6 of this paper.

Remarks begin on page 7 of this paper.